ABSTRACT

A semiconductor device may include first active patterns adjacent to each other on a substrate, first source/drain patterns respectively on the first active patterns and adjacent to each other, a first division structure and a second division structure crossing the first active patterns and arranged on the substrate such that adjacent ones of the first source/drain patterns are interposed between the first division structure and the second division structure, a first penetration via between adjacent ones of the first source/drain patterns, a first power line on the first penetration via and electrically connected to the first penetration via, a power delivery network layer on a bottom surface of the substrate, and a first lower penetration via between the power delivery network layer and the first penetration via.

FIG. 5F